BLF644P

Broadband power LDMOS transistor Rev. 1 — 11 June 2013

Objective data sheet

1. **Product profile**

1.1 General description

A 70 W LDMOS RF power transistor for broadcast transmitter and industrial applications. The transistor is suitable for the frequency range HF to 1300 MHz. The excellent ruggedness and broadband performance of this device makes it ideal for digital applications.

Table 1. **Typical performance**

RF performance at $T_{case} = 25$ °C in a common source test circuit.

Test signal	f	V _{DS}	P _L	Gp	η_{D}	IMD
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
CW, class-A	860	32	90	22	<tbd></tbd>	-
CW pulsed, class-AB	860	32	100	23.5	66	<tbd></tbd>
2-tone, class-AB	860	32	45	23	<tbd></tbd>	<tbd></tbd>

1.2 Features and benefits

- Integrated ESD protection
- Excellent ruggedness
- High power gain
- High efficiency
- Excellent reliability
- Easy power control
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- Communication transmitter applications in the HF to 1300 MHz frequency range
- Industrial applications in the HF to 1300 MHz frequency range



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2. Pinning information

Table 2. Pinning

Pin	Description	Simplified	doutline	Graphic symbol
1	drain1			1.4
2	drain2		2	3 →
3	gate1			5
4	gate2	3	4 5	4 7 2
5	source	[1]		aaa-005775

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	Package			
	Name	Description	Version		
BLF644P	-	flanged LDMOST ceramic package; 2 mounting holes; 4 leads	SOT1228A		

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		-			
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+11	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	200	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	T_{case} = 80 °C; P_L = 90 W	[1] <tbd></tbd>	K/W

^[1] $R_{th(j-c)}$ is measured under RF conditions.

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6. Characteristics

Table 6. DC characteristics

 $T_i = 25$ °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.5 \text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 32 \text{ V}; I_D = 50 \text{ mA}$	1.4	1.9	2.4	V
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 32 \text{ V}; I_{Dq} = 250 \text{ mA}$	1.5	2.0	2.5	V
I_{DSS}	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 32 \text{ V}$	-	-	1.4	μΑ
I_{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	9.0	-	Α
I_{GSS}	gate leakage current	$V_{GS} = \pm 10 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	50	nA
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 2.5 \text{ A}$	-	3.3	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 1.75 \text{ A}$	-	300	-	mΩ

Table 7. AC characteristics

 $T_i = 25$ °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C_{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 32 \text{ V}; f = 1 \text{ MHz}$	-	39	-	pF
Coss	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 32 \text{ V}; f = 1 \text{ MHz}$	-	15	-	pF
C _{rs}	feedback capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 32 \text{ V}; f = 1 \text{ MHz}$	-	0.84	-	pF

Table 8. RF characteristics

Test signal: CW pulsed, class-AB; f = 860 MHz; RF performance at $V_{DS} = 32$ V; $I_{Dq} = 200$ mA; $T_{case} = 25$ °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
G_p	power gain	$P_{L} = 100 \text{ W}$	23	23.5	-	dB
η_{D}	drain efficiency	$P_{L} = 100 \text{ W}$	61	66	-	%
RLin	input return loss	$P_{L} = 100 \text{ W}$	-	–15	-10	dBc

7. Test information

7.1 Ruggedness in class-AB operation

The BLF644P is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: $V_{DS} = 32 \text{ V}$; f = 1300 MHz at rated load power.

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8. Package outline

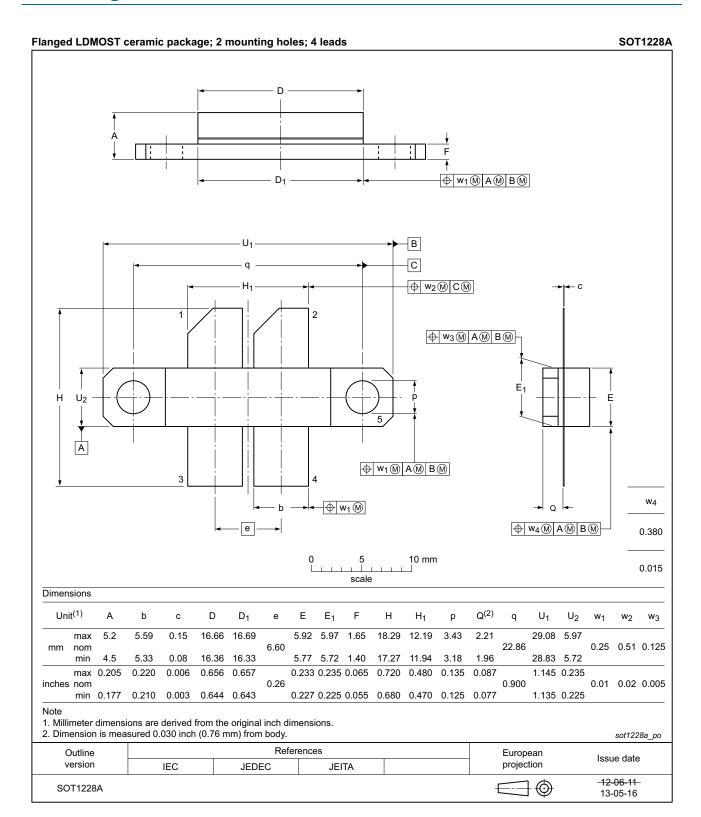


Fig 1. Package outline SOT1228A

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9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

10. Abbreviations

Table 9. Abbreviations

Acronym	Description
CW	Continuous Wave
ESD	ElectroStatic Discharge
HF	High Frequency
LDMOS	Laterally Diffused Metal Oxide Semiconductor
LDMOST	Laterally Diffused Metal Oxide Semiconductor Transistor
VSWR	Voltage Standing-Wave Ratio

11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF644P v.1	20130611	Objective data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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